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- Members of the Texas Instruments
 Widebus™ Family
- State-of-the-Art Advanced BiCMOS Technology (ABT) Design for 3.3-V Operation and Low Static-Power Dissipation
- 5-V I/O Compatible
- High Drive Capability (-32 mA/64 mA)
- Support Mixed-Mode Signal Operation (5-V Input and Output Voltages With 3.3-V V_{CC})
- Support Unregulated Battery Operation Down to 2.3 V
- Typical V_{OLP} (Output Ground Bounce)
 < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Auto3-State Eliminates Bus Current Loading When Voltage at the Output Exceeds V_{CC}
- I_{off} and Power-Up 3-State Support Hot Insertion
- Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors
- Latch-Up Performance Exceeds 250 mA Per JESD 17
- ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Package Options Include Plastic 300-mil Shrink Small-Outline (DL), Thin Shrink Small-Outline (DGG), Thin Very Small-Outline (DGV) Packages, and 380-mil Fine-Pitch Ceramic Flat (WD) Package

NOTE: For tape and reel order entry:
The DGGR package is abbreviated to GR, and the DGVR package is abbreviated to VR.

SN54ALVTH16244 . . . WD PACKAGE SN74ALVTH16244 . . . DGG, DGV, OR DL PACKAGE (TOP VIEW)

10E	1	U	48	20E
1Y1 [2		47	1A1
1Y2] 1A2
GND [4			GND
1Y3 🛚	5			1A3
1Y4 [6		43	1A4
v _{cc} [7] v _{cc}
2Y1 [8			2A1
2Y2 🛚	9		40	2A2
GND [10		39	GND
2Y3 [11			2A3
2Y4 [12		37] 2A4
3Y1	13		36	3A1
3Y2	14		35	3A2
GND [15		34	GND
3Y3 [16		33] 3A3
3Y4 🛚	17		32] 3A4
v _{cc} [18		31] v _{cc}
4Y1 [19		30] 4A1
4Y2 🛚	20		29] 4A2
GND [21		28	GND
4Y3 🛚	22		27] 4A3
4Y4 [23		26] 4A4
40E	24		25	30E
			#	0

description

The 'ALVTH16244 devices are 16-bit buffers/line drivers designed for 2.5-V or 3.3-V V_{CC} operation, but with the capability to provide a TTL interface to a 5-V system environment. These devices can be used as four 4-bit buffers, two 8-bit buffers, or one 16-bit buffer.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

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description (continued)

When V_{CC} is between 0 and 1.2 V, the device is in the high-impedance state during power up or power down. However, to ensure the high-impedance state above 1.2 V, the output-enable (\overline{OE}) input should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

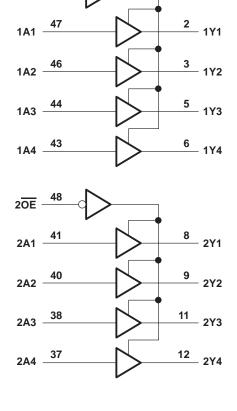
These devices are fully specified for hot-insertion applications using I_{off} and power-up 3-state. The I_{off} circuitry disables the outputs, preventing damaging current backflow through the devices when they are powered down. The power-up 3-state circuitry places the outputs in the high-impedance state during power up and power down, which prevents driver conflict.

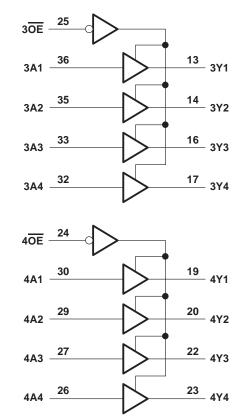
The SN54ALVTH16244 is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74ALVTH16244 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE (each buffer)

INPU	JTS	OUTPUT
ŌĒ	Α	Υ
L	Н	Н
L	L	L
Н	Χ	Z

logic diagram (positive logic)







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absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V _{CC}	
Input voltage range, V _I (see Note 1)	–0.5 V to 7 V
or power-off state, V _O (see Note 1)	0.5 V to 7 V
Voltage range applied to any output in the high state, V _O (see Note 1)	0.5 V to V _{CC} to 7V
Output current in the low state, I _O : SN54ALVTH16244	
Output current in the high state, I _O : SN54ALVTH16244	
Input clamp current, I _{IK} (V _I < 0)	
Output clamp current, I _{OK} (V _O < 0)	
Package thermal impedance, θ_{JA} (see Note 2): DGG package	
	93°C/W
DL package	94°C/W
Storage temperature range, T _{sta}	

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

2. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions, V_{CC} = 2.5 V \pm 0.2 V (see Note 3)

			SN54ALVT	TH16244	SN74ALVT	SN74ALVTH16244	
			MIN	MAX	MIN	MAX	UNIT
Vcc	Supply voltage		2.3	2.7	2.3	2.7	V
V _{IH}	High-level input voltage			2	1.7		V
V _{IL}	Low-level input voltage			0.7		0.7	V
VI	Input voltage			5.5	0	5.5	V
ЮН	High-level output current			_6		-8	mA
lai	Low-level output current		22	6		8	mA
lor	Low-level output current; current duty cycle ≤ 50%; f ≥	1 kHz	0	18		24	IIIA
Δt/Δν	Input transition rise or fall rate	Outputs enabled	Q	10		10	ns/V
Δt/ΔV _{CC}	Power-up ramp rate		200		200	·	μs/V
TA	Operating free-air temperature		-55	125	-40	85	°C

NOTE 3: All unused control inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.



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recommended operating conditions, V_{CC} = 3.3 V \pm 0.3 V (see Note 3)

			SN54ALV	ГН16244	SN74ALVT	UNIT	
			MIN	MAX	MIN	MAX	UNIT
VCC	Supply voltage		3	3.6	3	3.6	V
V _{IH}	High-level input voltage			3	2		V
V _{IL}	Low-level input voltage			8.0		0.8	V
VI	Input voltage			5.5	0	5.5	V
loh	High-level output current			-24		-32	mA
lai	Low-level output current		20	24		32	mA
lol	Low-level output current; current duty cycle ≤ 50%; f ≥	1 kHz	0	48		64	ША
Δt/Δν	Input transition rise or fall rate Outputs enabled		Q	10		10	ns/V
Δt/ΔV _{CC}	Power-up ramp rate		200		200		μs/V
TA	Operating free-air temperature		-55	125	-40	85	°C

NOTE 3: All unused control inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

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electrical characteristics over recommended operating free-air temperature range, V_{CC} = 2.5 V \pm 0.2 V (unless otherwise noted)

DAI	RAMETER	TEST CA	ONDITIONS	SN54	ALVTH1	6244	SN74	ALVTH1	6244	UNIT	
PAI	RAWETER	TEST CO	UNDITIONS	MIN	TYP†	MAX	MIN	TYP [†]	MAX	UNII	
V_{IK}		$V_{CC} = 2.3 \text{ V},$	$I_{I} = -18 \text{ mA}$			-1.2			-1.2	V	
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V},$	$I_{OH} = -100 \mu A$	V _{CC} -0	.2		V _{CC} -0	V _{CC} -0.2			
VOH		V _{CC} = 2.3 V	$I_{OH} = -6 \text{ mA}$	1.8						V	
		V(C = 2.5 V	$I_{OH} = -8 \text{ mA}$				1.8				
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V},$	I _{OL} = 100 μA			0.2			0.2		
			I _{OL} = 6 mA			0.4					
V_{OL}		V _{CC} = 2.3 V	I _{OL} = 8 mA						0.4	V	
		VCC = 2.5 V	I _{OL} = 18 mA			0.5					
	_		$I_{OL} = 24 \text{ mA}$						0.5		
	Control inputs	$V_{CC} = 2.7 \text{ V},$	$V_I = V_{CC}$ or GND			±1			±1		
1.	Control inputs	$V_{CC} = 0 \text{ or } 2.7 \text{ V},$	V _I = 5.5 V			\$ 10			10	μΑ	
Ħ		Vac - 2.7.V	$V_I = V_{CC}$		1			1			
	Data inputs	V _{CC} = 2.7 V	V _I = 0		PA	- 5			– 5		
l _{off}		$V_{CC} = 0$,	V_I or $V_O = 0$ to 4.5 V		1				±100	μΑ	
		V 22V	V _I = 0.7 V		3 115			115			
I _I (hold)	Data inputs	V _{CC} = 2.3 V	V _I = 1.7 V		-10			-10		μΑ	
, ,		$V_{CC} = 2.7 V^{\ddagger}$,	$V_{I} = 0 \text{ to } 2.7 \text{ V}$	Q		±300			±300		
I _{EX} §		$V_{CC} = 2.3 \text{ V},$	V _O = 5.5 V			125			125	μΑ	
IOZ(PU	_{/PD)} ¶	$V_{CC} \le 1.2 \text{ V}, V_{O} = \frac{0.5}{\text{OE}} \text{ V}$ V _I = GND or V _{CC} , $\overline{\text{OE}}$ =	/ to V _{CC} , : don't care			±100			±100	μΑ	
lozh		V _{CC} = 2.7 V	$V_O = 2.3 \text{ V},$ $V_I = 0.7 \text{ V or } 1.7 \text{ V}$			5			5	μΑ	
l _{OZL}		V _{CC} = 2.7 V	$V_O = 0.5 \text{ V},$ $V_I = 0.7 \text{ V or } 1.7 \text{ V}$			- 5			-5	μΑ	
		V _{CC} = 2.7 V,	Outputs high		0.04	0.1		0.04	0.1		
ICC		$I_{O} = 0$,	Outputs low		2.3	4.5		2.3	4.5	mA	
		$V_I = V_{CC}$ or GND	Outputs disabled		0.04	0.1		0.04	0.1		
Ci		$V_{CC} = 2.5 \text{ V},$	V _I = 2.5 V or 0		3			3		pF	
Со		$V_{CC} = 2.5 \text{ V},$	V _O = 2.5 V or 0		6			6		pF	

[†] All typical values are at $V_{CC} = 2.5 \text{ V}$, $T_A = 25^{\circ}\text{C}$.



[‡] This is the bus-hold maximum dynamic current. It is the minimum overdrive current required to switch the input from one state to another.

 $[\]S$ Current into an output in the high state when $V_O > V_{CC}$

[¶] High-impedance state during power up/power down

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electrical characteristics over recommended operating free-air temperature range, V_{CC} = 3.3 V \pm 0.3 V (unless otherwise noted)

DAD	AMETED	TEST CO	NDITIONS	SN54	ALVTH1	6244	SN74ALVTH16244		6244	UNIT	
PAR	RAMETER	lESI CO	NDITIONS	MIN	TYP	MAX	MIN	TYP	MAX	UNIT	
VIK		$V_{CC} = 3 V$,	$I_{I} = -18 \text{ mA}$			-1.2			-1.2	V	
		$V_{CC} = 3 \text{ V to } 3.6 \text{ V},$	I _{OH} = -100 μA	V _{CC} -0.	2		V _{CC} -0.	.2			
VOH	V 0V	I _{OH} = -24 mA	2						V		
		VCC = 3 V	$I_{OH} = -32 \text{ mA}$				2				
		$V_{CC} = 3 \text{ V to } 3.6 \text{ V},$	I _{OL} = 100 μA			0.2			0.2		
			I _{OL} = 16 mA						0.4		
V0:			I _{OL} = 24 mA			0.5				V	
VOL		V _{CC} = 3 V	I _{OL} = 32 mA						0.5	V	
			I _{OL} = 48 mA			0.55					
			I _{OL} = 64 mA						0.55		
	Control inputs	V _{CC} = 3.6 V,	$V_I = V_{CC}$ or GND			±1			±1		
ı [Control inputs	$V_{CC} = 0 \text{ or } 3.6 \text{ V},$	V _I = 5.5 V			10			10		
l _l		ta inputs V _{CC} = 3.6 V	V _I = 5.5 V			20			20	μΑ	
Data inputs	Data inputs		VI = VCC	1					1		
			V _I = 0		EL.	- 5			– 5		
l _{off}		$V_{CC} = 0$,	V_I or $V_O = 0$ to 4.5 V		Q				±100	μΑ	
		V _{CC} = 3 V	V _I = 0.8 V	75	, ,		75				
I _{I(hold)}	Data inputs		V _I = 2 V	-75	20		-75			μΑ	
		$V_{CC} = 3.6 V^{\ddagger}$,	$V_{I} = 0 \text{ to } 3.6 \text{ V}$	B		±500			±500		
I _{EX} §		$V_{CC} = 3 V$,	V _O = 5.5 V			125			125	μΑ	
I _{OZ(PU/I}	PD) [¶]	$V_{CC} \le 1.2 \text{ V}, V_{O} = \underline{0.5} \text{ V}$ V _I = GND or V_{CC} , $\overline{OE} = 0.5 \text{ V}$	to V _{CC} , don't care			±100			±100	μА	
lozh		V _{CC} = 3.6 V	V _O = 3 V, V _I = 0.8 V or 2 V			5			5	μА	
lozL		V _{CC} = 3.6 V	V _O = 0.5 V, V _I = 0.8 V or 2 V			- 5			-5	μА	
		V _{CC} = 3.6 V,	Outputs high		0.07	0.1		0.07	0.1		
ICC		$I_{O} = 0$,	Outputs low		3.2	5		3.2	5	mA	
V _I = V _{CC} or GND Outputs disabled	Outputs disabled		0.07	0.1		0.07	0.1				
ΔI _{CC} #		V _{CC} = 3 V to 3.6 V, One Other inputs at V _{CC} or G				0.4			0.4	mA	
Ci		V _{CC} = 3.3 V,	V _I = 3.3 V or 0		3			3		pF	
Со		V _{CC} = 3.3 V,	V _O = 3.3 V or 0		6			6		pF	

[†] All typical values are at $V_{CC} = 3.3 \text{ V}$, $T_A = 25^{\circ}\text{C}$.



[‡]This is the bus-hold maximum dynamic current. It is the minimum overdrive current required to switch the input from one state to another.

 $[\]S$ Current into an output in the high state when $V_O > V_{CC}$

[¶] High-impedance state during power up/power down

[#] This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

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switching characteristics over recommended operating free-air temperature range, C_L = 30 pF, V_{CC} = 2.5 V \pm 0.2 V (unless otherwise noted) (see Figure 1)

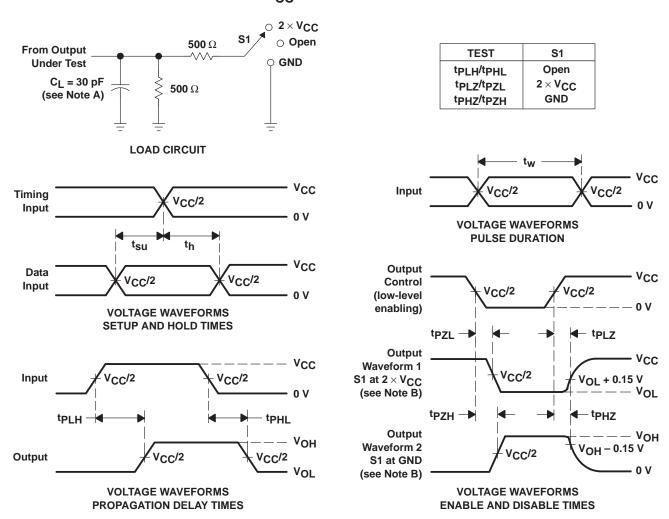
PARAMETER	FROM	FROM TO SN54ALVTH16244		H16244	SN74ALVT	UNIT	
FARAIVIETER	(INPUT)	(OUTPUT)	MIN	MAX	MIN	MAX	UNII
^t PLH	۸	V	1	3.1	1	3	ns
^t PHL	А	ı	1	3.6	1	3.5	115
^t PZH	-		1.1	6	1.1	5.9	ns
^t PZL	OE	ı	1.150	4.8	1.1	4.7	115
^t PHZ	<u> </u>	V	1,5	4.5	1.5	4.4	ns
t _{PLZ}	OE	'	& ^C 1	3.5	1	3.4	113

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF, V_{CC} = 3.3 V \pm 0.3 V (unless otherwise noted) (see Figure 2)

PARAMETER	FROM	то	SN54ALVTH16244		SN74ALVT	UNIT	
PARAMETER	(INPUT)	(OUTPUT)	MIN	MAX	MIN	MAX	UNII
t _{PLH}	Δ.	V	1	2.6	1	2.4	
t _{PHL}	А	ī	1	2.6	1	2.5	ns
^t PZH	<u></u>	V	1,	3.9	1	3.8	ns
t _{PZL}	ŌĒ	ı	30	3	1	2.9	115
^t PHZ	ŌĒ	٧	1.5	4.3	1.5	4.2	ns
t _{PLZ}	OE	'	1.5	3.7	1.5	3.6	113

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PARAMETER MEASUREMENT INFORMATION $V_{CC} = 2.5 \text{ V} \pm 0.2 \text{ V}$



NOTES: A. C_L includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, Z_{Ω} = 50 Ω , $t_r \leq$ 2 ns, $t_f \leq$ 2 ns.
- D. The outputs are measured one at a time with one transition per measurement.

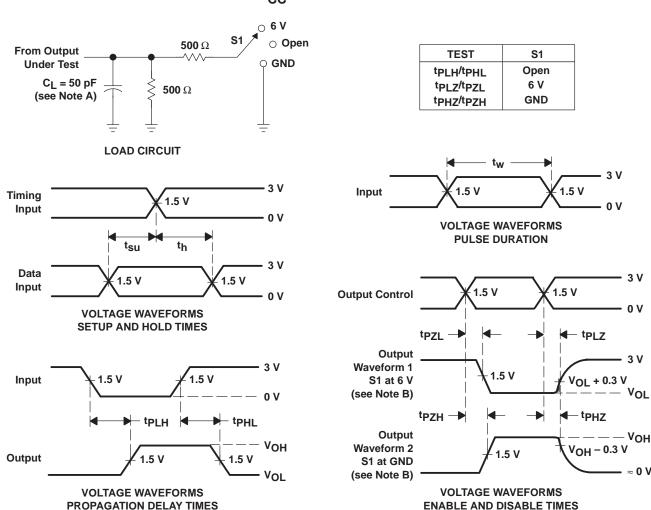
Figure 1. Load Circuit and Voltage Waveforms



LOW- AND HIGH-LEVEL ENABLING

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PARAMETER MEASUREMENT INFORMATION $V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$



NOTES: A. C_L includes probe and jig capacitance.

INVERTING AND NONINVERTING OUTPUTS

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_O = 50 \Omega$, $t_f \leq$ 2.5 ns. $t_f \leq$ 2.5 ns.
- D. The outputs are measured one at a time with one transition per measurement.

Figure 2. Load Circuit and Voltage Waveforms



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